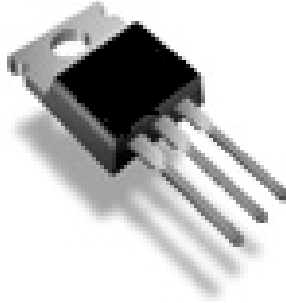




Description

The Bay Linear n-channel power field effect transistors are produced using high cell density DMOS technology , These devices are particularly suited for low voltage applications such as automotive and other battery powered circuits where fast switching, low in-line power loss and resistance to transistors are needed.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 watts. Also, available in a D² surface mount power package with a power dissipation up to 2 Watts



Features

- **Critical DC Electrical parameters specified at elevated Temp.**
- **Rugged internal source-drain diode can eliminate the need for external Zener diode transient suppresser**
- **Super high density cell design for extremely low R_{DS(ON)}**

$$V_{DSS} = 30V$$

$$R_{DS(ON)} = 0.013 \Omega$$

$$I_D = 52A$$

Ordering Information

Device	Package	Temp.
50N035T	TO-220	0 to 150°C
50N035S	TO-263 (D ²)	0 to 150°C

Absolute Maximum Rating

Symbol	Parameter	Max	Unit
I _D	Drain Current	52	A
	Continues		
	Pulsed		
V _{DSS}	Drain-Source Voltage	30	V
V _{GSV}	Gate Source Voltage	±20	V
P _D	Total Power Dissipation @ T _C =25°C	50	W
	Derate above 25°C	0.4	W/°C
T _J	Operating and Storage	-65 to 175	°C
T _{STG}	Temperature Range		

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24V$ $V_{GS}=0V$			10	μA
I_{GBLF}	Gate-Body Leakage Forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
I_{GBLR}	Gate-Body Leakage Reverse	$V_{GS}=20V, V_{DS}=0V$			-100	nA
ON CHARACTERISTICS						
V_{GS}	Gate Threshold Voltage	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1		3	V
$R_{DS(ON)}$	Static Drain Voltage	$V_{GS}=10V, I_D=26A$ $V_{CS}=4.5V, I_O=21A$			0.013 0.018	Ω
$I_{D(ON)}$	ON-State Drain Current	$V_{GS}=10V$	52			A
g_{fs}	Forward Transconductance			32		
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V$ $F=1.0\text{ MHz}$			1800	pF
C_{OSS}	Output Capacitance				1000	pF
C_{RSS}	Reverse Trans. Capacitance				500	pF
SWITCHING CHARACTERISTICS						
$t_{D(ON)}$	Turn-ON Delay Time	$V_{DD}=15V$ $I_D=52A, V_{DS}=10V$ $R_{GEN}=25\Omega$			25	nS
t_r	Turn-ON Rise Time				200	
$t_{d(off)}$	Turn-OFF Delay Time				50	
t_f	Turn-OFF Fall Time				120	
SOURCE DRAIN DIODE CHARACTERISTICS						
I_S	Maxim Continuous Drain source Diode Forward Current				52	A
$V_{DS}(\text{note})$	Drain Source Diode Forward Voltage	$V_{GS}=0V$ $I_S=26A$			1.30	V
THERMAL CHARACTERISTICS						
R_{JC}	Thermal Resistance, Junction to Case				2.5	$^\circ\text{C/W}$
R_{JA}	Thermal Resistance, Junction to Ambient				62.5	$^\circ\text{C/W}$

Note: Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Advance Information- These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

Preliminary Information- These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

The application circuit examples are only to explain the representative applications of the devices and are not intended to guarantee any circuit design or permit any industrial property right to other rights to execute. Bay Linear takes no responsibility for any problems related to any industrial property right resulting from the use of the contents shown in the data book. Typical parameters can and do vary in different applications. Customer's technical experts must validate all operating parameters including "Typical" for each customer application.

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